Triple Inverter

The NL37WZ04 is a high performance triple inverter operating from a 1.65 V to 5.5 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance.

- Extremely High Speed: t_{PD} 2.0 ns (typical) at $V_{CC} = 5$ V
- Designed for 1.65 V to 5.5 V V_{CC} Operation
- Over Voltage Tolerant Inputs and Outputs
- $\bullet\,$ LVTTL Compatible Interface Capability With 5 V TTL Logic with V_{CC} = 3 V
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current Substantially Reduces System Power Requirements
- Chip Complexity: FET = 72

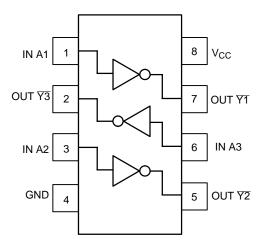


Figure 1. Pinout (Top View)

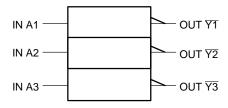


Figure 2. Logic Symbol



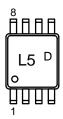
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MARKING DIAGRAM



US8 US SUFFIX CASE 493-01



D = Date Code

PIN ASSIGNMENT

1	IN A1
2	OUT Y 3
3	IN A2
4	GND
5	OUT Y2
6	IN A3
7	OUT Y1
8	V _{CC}

FUNCTION TABLE

A Input	▼ Output
L	Н
Н	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
V _I	DC Input Voltage		-0.5 to +7.0	V
Vo	DC Output Voltage		-0.5 to +7.0	V
I _{IK}	DC Input Diode Current	-50	mA	
I _{OK}	DC Output Diode Current	-50	mA	
I _O	DC Output Sink Current	±50	mA	
I _{CC}	DC Supply Current per Supply Pin	±100	mA	
I _{GND}	DC Ground Current per Ground Pin		±100	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds	3	260	°C
TJ	Junction Temperature under Bias		+150	°C
θ_{JA}	Thermal Resistance	(Note 1)	250	°C/W
P _D	Power Dissipation in Still Air at 85°C		250	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 N/A	V

Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum–rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

- Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
 Tested to EIA/JESD22-A114-A.
- 3. Tested to EIA/JESD22-A115-A.
- 4. Tested to JESD22-C101-A.

RECOMMENDED OPERATING CONDITIONS

Symbol	Paramete	Min	Max	Unit	
V _{CC}	Supply Voltage	Operating Data Retention Only	1.65 1.5	5.5 5.5	V
VI	Input Voltage	(Note 5)	0	5.5	V
Vo	Output Voltage	(HIGH or LOW State)	0	V _{CC}	V
T _A	Operating Free–Air Temperature		-40	+85	°C
Δt/ΔV	Input Transition Rise or Fall Rate	$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$ $V_{CC} = 3.0 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0 0 0	20 10 5	ns/V

^{5.} Unused inputs may not be left open. All inputs must be tied to a high- or low-logic input voltage level.

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	T _A = 25°C			$-40^{\circ}\text{C} \leq \text{T}_{\text{A}} \leq 85^{\circ}\text{C}$		
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Unit
V _{IH}	High-Level Input Voltage		1.65	0.75 V _{CC}			0.75 V _{CC}		V
			2.3 to 5.5	0.7 V _{CC}			0.7 V _{CC}		
V _{IL}	Low-Level Input Voltage		1.65			0.25 V _{CC}		0.25 V _{CC}	V
			2.3 to 5.5			0.3 V _{CC}		0.3 V _{CC}	
V _{OH}	High-Level Output Volt-	I _{OH} = -100 μA	1.65 to 5.5	V _{CC} -0.1	V _{CC}		V _{CC} −0.1		V
	age V _{IN} = V _{IL}	$I_{OH} = -3 \text{ mA}$	1.65	1.29	1.52		1.29		
	- 114 - 112	$I_{OH} = -8 \text{ mA}$	2.3	1.9	2.1		1.9		
		$I_{OH} = -12 \text{ mA}$	2.7	2.2	2.4		2.2		
		$I_{OH} = -16 \text{ mA}$	3.0	2.4	2.7		2.4		
		$I_{OH} = -24 \text{ mA}$	3.0	2.3	2.5		2.3		
		$I_{OH} = -32 \text{ mA}$	4.5	3.8	4.0		3.8		
V _{OL}	Low-Level Output Volt-	I _{OL} = 100 μA	1.65 to 5.5			0.1		0.1	V
	age V _{IN} = V _{IH}	I _{OL} = 3 mA	1.65		0.08	0.24		0.24	
		I _{OL} = 8 mA	2.3		0.20	0.3		0.3	
		I _{OL} = 12 mA	2.7		0.22	0.4		0.4	
		I _{OL} = 16 mA	3.0		0.28	0.4		0.4	
		I _{OL} = 24 mA	3.0		0.38	0.55		0.55	
		I _{OL} = 32 mA	4.5		0.42	0.55		0.55	
I _{IN}	Input Leakage Current	$V_{IN} = V_{CC}$ or GND	0 to 5.5			± 0.1		±1.0	μΑ
l _{OFF}	Power Off–Output Leakage Current	V _{OUT} = 5.5 V	0			1		10	μΑ
I _{CC}	Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	1.65 to 5.5			1		10	μΑ

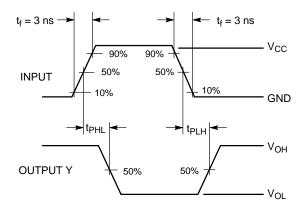
AC ELECTRICAL CHARACTERISTICS t_R = t_F = 2.5 ns; C_L = 50 pF; R_L = 500 Ω

			V _{cc}	T _A = 25°C		$-40^{\circ}C \leq T_{A} \leq 85^{\circ}C$			
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Unit
t _{PLH}	Propagation Delay	$R_L = 1 \text{ M}\Omega$, $C_L = 15 \text{ pF}$	1.8 ± 0.15	1.8	4.4	9.5	2.0	10	ns
t _{PHL}	(Figure 3 and 4)	$R_L = 1 \text{ M}\Omega$, $C_L = 15 \text{ pF}$	2.5 ± 0.2	1.2	5.0	5.7	1.2	6.1	
		$R_L = 1 \text{ M}\Omega$, $C_L = 15 \text{ pF}$	3.3 ± 0.3	0.8	2.2	3.4	0.8	3.8	
		$R_L = 500 \Omega, C_L = 50 pF$		1.2	3.9	4.5	1.2	5.0	
		$R_L = 1 \text{ M}\Omega$, $C_L = 15 \text{ pF}$	5.0 ± 0.5	0.5	18	2.8	0.5	3.1	
		$R_L = 500 \Omega, C_L = 50 pF$		0.8	2.3	3.6	0.8	4.0	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	$V_{CC} = 5.5 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	2.5	pF
C _{PD}	Power Dissipation Capacitance	10 MHz, V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	9	pF
	(Note 6)	10 MHz, V _{CC} = 5.5 V, V _I = 0 V or V _{CC}	11	

^{6.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC} \cdot C_{PD}$ is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.



 $^{\star}\text{C}_{\text{L}}$ includes all probe and jig capacitances.

A 1–MHz square input wave is recommended for propagation delay tests.

Figure 3. Switching Waveform

Figure 4. Test Circuit

DEVICE ORDERING INFORMATION

			Device No	menclature				
Device Order Number	Logic Circuit Indicator	No. of Gates per Package	Temp Range Identifier	Technology	Device Function	Package Suffix	Package Type	Tape and Reel Size
NL37WZ04US	NL	3	7	WZ	04	US	US8	178 mm, 3000 Unit

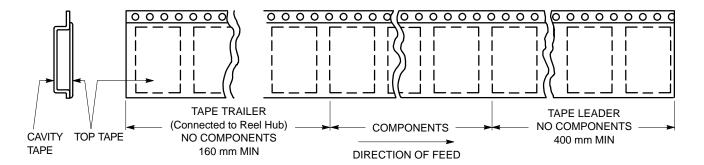


Figure 5. Tape Ends for Finished Goods

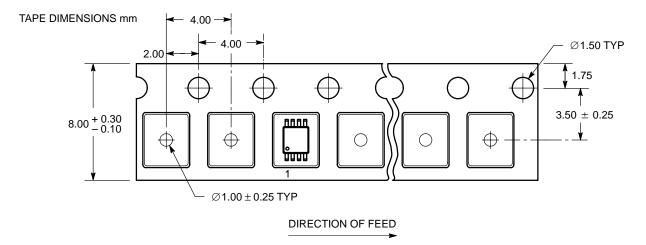


Figure 6. US8 Reel Configuration/Orientation

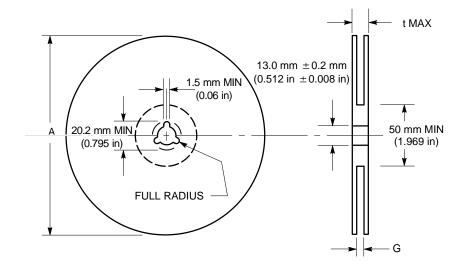


Figure 7. Reel Dimensions

REEL DIMENSIONS

Tape Size	T and R Suffix	A Max	G	t Max
8 mm	US	178 mm (7 in)	8.4 mm, + 1.5 mm, -0.0 (0.33 in + 0.059 in, -0.00)	14.4 mm (0.56 in)

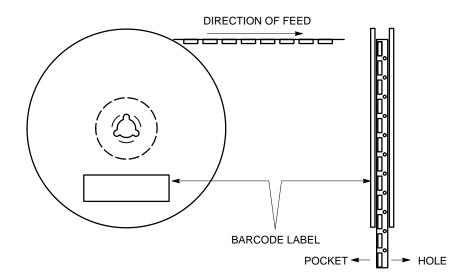
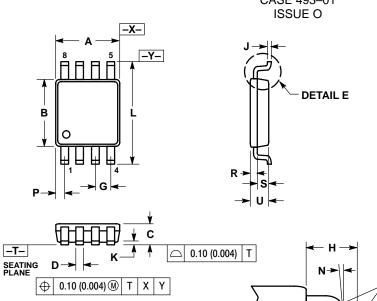


Figure 8. Reel Winding Direction

PACKAGE DIMENSIONS

US8 **US SUFFIX** CASE 493-01



R 0.10 TYP

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETERS

 3. DIMENSION "A" DOES NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURR. MOLD FLASH. PROTRUSION AND GATE BURR SHALL NOT EXCEED 0.140 MM (0.0055") PER SIDE.

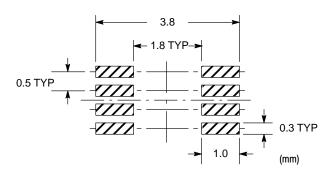
 4. DIMENSION "B" DOES NOT INCLUDE INTER-LEAD FLASH OR PROTRUSION. INTER-LEAD FLASH AND PROTRUSION SHALL NOT E3XCEED 0.140 (0.0055") PER SIDE.

 5. LEAD FINISH IS SOLDER PLATING WITH THICKNESS OF 0.0076-0.0203 MM. (300-800 INCH).

- INCH).

 6. ALL TOLERANCE UNLESS OTHERWISE SPECIFIED ±0.0508 (0.0002").

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	1.90	2.10	0.075	0.083	
В	2.20	2.40	0.087	0.094	
С	0.60	0.90	0.024	0.035	
D	0.17	0.25	0.007	0.010	
F	0.20	0.35	0.008	0.014	
G	0.50	BSC	0.020) BSC	
Н	0.40	REF	0.016 REF		
J	0.10	0.18	0.004	0.007	
K	0.00	0.10	0.000	0.004	
L	3.00	3.20	0.118	0.126	
M	0 °	6 °	0 °	6°	
N	5°	10 °	5 °	10 °	
P	0.28	0.44	0.011	0.017	
R	0.23	0.33	0.009	0.013	
S	0.37	0.47	0.015	0.019	
U	0.60	0.80	0.024	0.031	
V	0.12	BSC	0.00	BSC	



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